

Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition
1 BRS	L1	1253	((fixed ground)adj2 (potential voltage reference))and (soi silicon adj1 insulator)	USPAT; US-PGP UB	2002/09/12 16:58		
2 BRS	L2	211	((source and drain)same 1 (shall\$4 deep\$3 depth))and	USPAT; US-PGP UB	2002/09/12 16:58		
3 BRS	L3	198	2 and (partial\$3 groov\$3 shallow trench\$2 sti pti isolation\$2)	USPAT; US-PGP UB	2002/09/12 16:59		
4 BRS	L4	62	((deplet\$3) near\$5 (partial\$2 full\$3))and 3	USPAT; US-PGP UB	2002/09/12 16:46		
5 BRS	L5	62	(@ad<=200101107)and 4	USPAT; US-PGP UB	2002/09/12 16:59		
6 BRS	L6	51	((fixed ground)adj2 (potential voltage reference))and (soi silicon adj1 insulator)	EPO; JPO; DERWEN T; IBM_TD B	2002/09/12 16:50		
7 BRS	L7	0	((source and drain)and (shall\$4 deep\$3 depth))and 6	EPO; JPO; DERWEN T; IBM_TD B	2002/09/12 16:51		

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8	BRS	L8	11	(source and drain)and 6	EPO; JPO; DERWEN T; IBM_TD B	2002/09/12 16:52		
9	BRS	L9	5	6 and (partial\$3 groov\$3 shallow trench\$2 sti pti isolation\$2)	EPO; JPO; DERWEN T; IBM_TD B	2002/09/12 16:56		
10	BRS	L10	8025	(soi silicon adj1 insulator)	USPAT; US-PGP UB	2002/09/12 16:58		
11	BRS	L11	927	((source and drain) same (shall\$4 deep\$3 depth))and 10	USPAT; US-PGP UB	2002/09/12 16:58		
12	BRS	L12	89	((source and drain)with (shall\$4 deep\$3 depth))same (deplet\$4))and 10	USPAT; US-PGP UB	2002/09/12 16:59		
13	BRS	L13	84	12 and (partial\$3 groov\$3 shallow trench\$2 sti pti isolation\$2)	USPAT; US-PGP UB	2002/09/12 16:59		
14	BRS	L14	84	(@ad<=200101107)and 13	USPAT; US-PGP UB	2002/09/12 17:00		
15	BRS	L15	67	14 not 5	USPAT; US-PGP UB	2002/09/12 17:00		